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Lecture - 8 .
Review . > Jill now looked at NMUP, 7MUS characteristics (plots and equations)
        - Built a CMUS inventor, analysed and characterized (Matic & agramic) using
           simulations, equations and intuition
        -> with INVX1, other logic gots like NANDXI, NORXI, NANDX2, CR. con be durigated
        L) Given any new "device" (offer than an NMOS or 1MOS), the same set of skys can
           he und to durigm, analyse and characterize logic gates in a given tecanology
Front of synthesis <
     (gate-Level Nothist (RTL)
Barro Physical Duign &
 end Physical Geometries
 Ez
        HDL
                                            RTL
                                                                           NAND in LIBRARY
  module myderign (
                                     module myderign (
                                                                         nodule NAMIDXI ( - )
  ifut.
                                     ifut.
                                     ifut.
                                                                        on that
   Subduign1 41(. ),
Subduign1 42(. );
                                      Subduign1 41 (.
                                       Subduign (41(.))
                                                                          Y= ~(APB)
                                                                          nd module
 end module
                                    end module
                                                                        module NORXI
  module Subderign1 (
                                     module Subderign1 (
  Put . ,
                                     12ut . ,
                                     outfut - )
     an.g. Y = . ,
                                      HAMIDYI MIC
```

: Library [also called standard cell library] will contain functional definition (.v or .vhd) of all the logic gates (also called standard cells) 4) The V/Vhd Views of the standard alls provide functional definition for vimelation at the higher abstraction level (Conferred to MOSFET level dimulation) > This enables farter debugging (we don't have to fix bugg at the HUSFET level () This enables farter simulation (MUSFET level effice simulation for billion gates as

DFF 01(

end module

Cells from Library

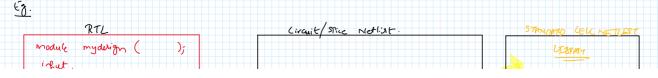
YERY YERY YERY YERY YERY SLOW

Functional definition of there

(in the form of ov or . Yha)

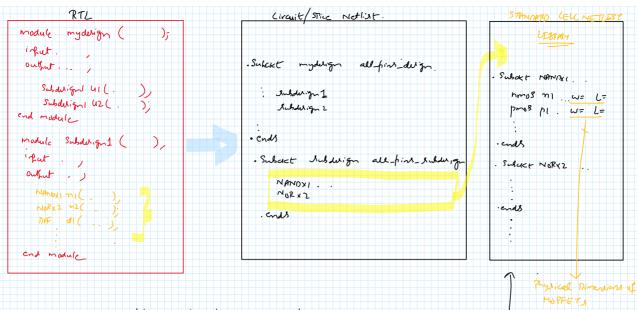
Cell are brount in the library

- * However, tremember that for final fabrication, we need the physical MOPFET and interconnect geometrics. This detail is incofforted in the spice netlist and layout.
- + The transformation from RTL to physical geometry is performed by the "Physical Durgn" tool. The tool needs account o individual spice next int layout of the logic gots (standard alls)



always C

end module.



* We also need physical layout of the circuit defined in the notice for fabrication This layout is saved in gds I format

. I go a standard (ell Library", we need to have atteast the following "views" of the standard (ells (logic cells)

. V or . Yhd . Cir/. spc/. sp/. cal

· gdsIT

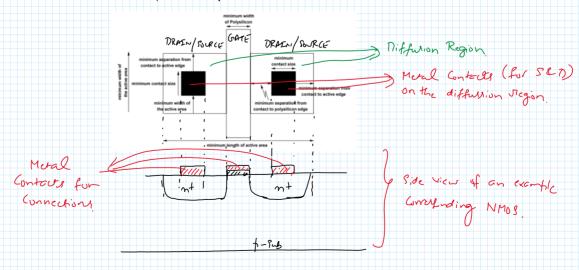
* . V . What can be carrily written and verified

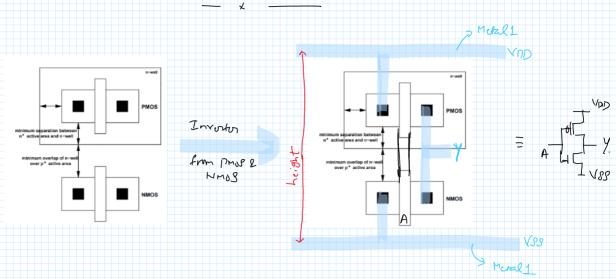
* Assignment - I Cover the Greation of Mice netfirst for Cogic cells.

I we will how disturs the treation of the legant

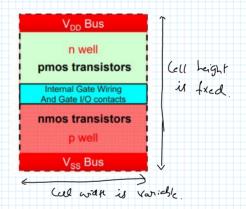
I hayout is done wing the top-view of the chip since the during parameters we have botter observed from the top- view than the side view



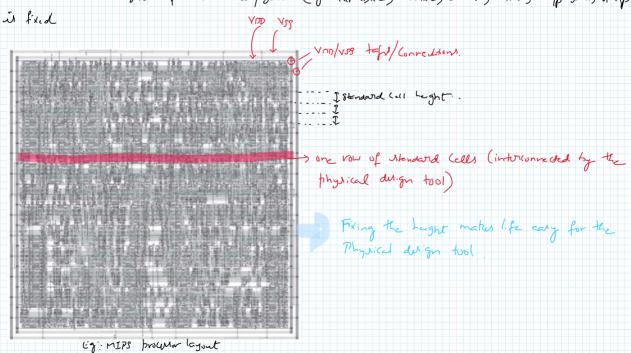




+ The height of a standard (cel is fixed for a given technology (offinized) The height must be fixed to allow the physical duign tool to make connections between cells and converge in a fartor way



ic the cell height of all cells/gots (gi-NMVDXZ, NORXZ, ENVXZ, DFF, 3-i/p gets, h-i/p gets) etc



I helmo drawing standard (ell un a softwar it is usually simulied on hen & has n

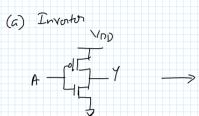
+ Before drawing standard (all on a software, it is usually visualized on pen & paper wing "STECK DEAGRAM".

Condidur the following Colour Coding:



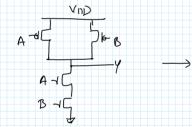
N diffusion
Polycilicon

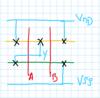
X (ontact.



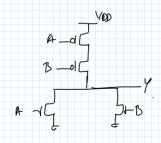


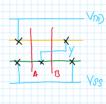
(b) 2-ilp NAND





(c) 2 ilp NOR





d) h-i/p NAMD & h-i/p NOR: - try it by yourself